

# FGW30N60VD

Discrete IGBT

## Discrete IGBT (High-Speed V series)

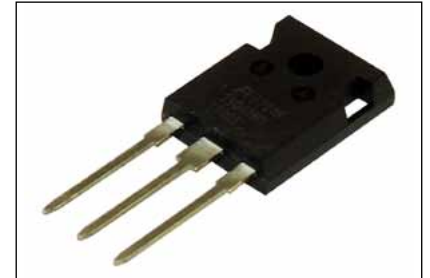
### 600V / 30A

#### ■ Features

- Low power loss
- Low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)

#### ■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply



#### ■ Maximum Ratings and Characteristics

##### ● Absolute Maximum Ratings (at T<sub>c</sub>=25°C unless otherwise specified)

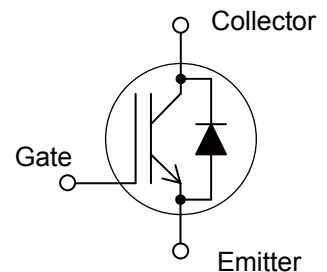
| Items                          | Symbols             | Characteristics | Units | Remarks  |
|--------------------------------|---------------------|-----------------|-------|--|
| Collector-Emitter voltage      | V <sub>CEs</sub>    | 600             | V     |  |
| Gate-Emitter voltage           | V <sub>GES</sub>    | ±20             | V     |  |
| DC Collector Current           | I <sub>C@25</sub>   | 55              | A     | T <sub>c</sub> =25°C, T <sub>j</sub> =150°C                          |
|                                | I <sub>C@100</sub>  | 30              | A     | T <sub>c</sub> =100°C, T <sub>j</sub> =150°C                         |
| Pulsed Collector Current       | I <sub>CP</sub>     | 60              | A     | Note *1  |
| Turn-Off Safe Operating Area   | -                   | 60              | A     | V <sub>CE</sub> ≤600V, T <sub>j</sub> ≤175°C                         |
| Diode Forward Current          | I <sub>F@25</sub>   | 48              | A     |  |
|                                | I <sub>F@100</sub>  | 25              | A     |  |
| Diode Pulsed Current           | I <sub>FP</sub>     | 60              | A     | Note *1  |
| Short Circuit Withstand Time   | t <sub>sc</sub>     | 10              | μs    | V <sub>CE</sub> ≤320V, V <sub>GE</sub> =15V<br>T <sub>j</sub> ≤150°C |
| IGBT Max. Power Dissipation    | P <sub>D_IGBT</sub> | 230             | W     | T <sub>c</sub> =25°C   |
| FWD Max. Power Dissipation     | P <sub>D_FWD</sub>  | 125             | W     | T <sub>c</sub> =25°C   |
| Operating Junction Temperature | T <sub>j</sub>      | -40~+175        | °C    |  |
| Storage Temperature            | T <sub>stg</sub>    | -55~+175        | °C    |  |

Note \*1 : Pulse width limited by T<sub>jmax</sub>.

##### ● Electrical characteristics (at T<sub>j</sub>= 25°C unless otherwise specified)

| Items                                | Symbols               | Conditions  | Characteristics       |      |      | Unit |    |
|--------------------------------------|-----------------------|---|-----------------------|------|------|------|----|
|                                      |                       |   | min.                  | typ. | max. |      |    |
| Collector-Emitter Breakdown Voltage  | V <sub>BR(ICES)</sub> | I <sub>c</sub> = 250μA, V <sub>GE</sub> = 0V                            | 600                   | -    | -    | V    |    |
| Zero Gate Voltage Collector Current  | I <sub>CEs</sub>      | V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0V                            | T <sub>j</sub> =25°C  | -    | -    | 250  | μA |
|                                      |                       |   | T <sub>j</sub> =175°C | -    | -    | 10   | mA |
| Gate-Emitter Leakage Current         | I <sub>GES</sub>      | V <sub>CE</sub> = 0V, V <sub>GE</sub> = ±20V                            | -                     | -    | -    | 200  | nA |
| Gate-Emitter Threshold Voltage       | V <sub>GE(th)</sub>   | V <sub>CE</sub> = +20V, I <sub>c</sub> = 30mA                           | 6.2                   | 6.7  | 7.2  | V    |    |
| Collector-Emitter Saturation Voltage | V <sub>CE(sat)</sub>  | V <sub>GE</sub> = +15V, I <sub>c</sub> = 30A                            | T <sub>j</sub> =25°C  | -    | 1.60 | 2.05 | V  |
|                                      |                       |   | T <sub>j</sub> =175°C | -    | 2.1  | -    |    |
| Input Capacitance                    | C <sub>ies</sub>      | V <sub>CE</sub> =25V  | -                     | 1910 | -    | pF   |    |
| Output Capacitance                   | C <sub>oes</sub>      | V <sub>GE</sub> =0V   | -                     | 145  | -    |      |    |
| Reverse Transfer Capacitance         | C <sub>res</sub>      | f=1MHz  | -                     | 105  | -    |      |    |
| Gate Charge                          | Q <sub>G</sub>        | V <sub>CC</sub> = 400V<br>I <sub>c</sub> = 30A<br>V <sub>GE</sub> = 15V | -                     | 225  | -    | nC   |    |
| Turn-On Delay Time                   | t <sub>d(on)</sub>    | T <sub>j</sub> = 25°C   | -                     | 35   | -    | ns   |    |
| Rise Time                            | t <sub>r</sub>        | V <sub>CC</sub> = 400V  | -                     | 60   | -    |      |    |
| Turn-Off Delay Time                  | t <sub>d(off)</sub>   | I <sub>c</sub> = 30A  | -                     | 200  | -    |      |    |
| Fall Time                            | t <sub>f</sub>        | V <sub>GE</sub> = 15V   | -                     | 38   | -    |      |    |
| Turn-On Energy                       | E <sub>on</sub>       | R <sub>G</sub> = 10Ω  | -                     | 1.2  | -    | mJ   |    |
| Turn-Off Energy                      | E <sub>off</sub>      | L = 500μH<br>Energy loss include "tail" and FWD reverse recovery.       | -                     | 0.7  | -    |      |    |
| Turn-On Delay Time                   | t <sub>d(on)</sub>    | T <sub>j</sub> = 175°C  | -                     | 36   | -    | ns   |    |
| Rise Time                            | t <sub>r</sub>        | V <sub>CC</sub> = 400V  | -                     | 60   | -    |      |    |
| Turn-Off Delay Time                  | t <sub>d(off)</sub>   | I <sub>c</sub> = 30A  | -                     | 235  | -    |      |    |
| Fall Time                            | t <sub>f</sub>        | V <sub>GE</sub> = 15V   | -                     | 50   | -    |      |    |
| Turn-On Energy                       | E <sub>on</sub>       | R <sub>G</sub> = 10Ω  | -                     | 2.0  | -    | mJ   |    |
| Turn-Off Energy                      | E <sub>off</sub>      | L = 500μH<br>Energy loss include "tail" and FWD reverse recovery.       | -                     | 1.2  | -    |      |    |
| Forward Voltage Drop                 | V <sub>F</sub>        | I <sub>F</sub> =25A   | T <sub>j</sub> =25°C  | -    | 1.5  | 1.95 | V  |
|                                      |                       |   | T <sub>j</sub> =175°C | -    | 1.3  | -    | V  |
| Diode Reverse Recovery Time          | t <sub>rr1</sub>      | V <sub>CC</sub> =30V<br>I <sub>F</sub> = 2.5A<br>-di/dt=200A/μs         | -                     | 40   | 52   | ns   |    |
| Diode Reverse Recovery Time          | t <sub>rr2</sub>      | V <sub>CC</sub> =400V<br>I <sub>F</sub> =25A                            | -                     | 0.30 | -    | μs   |    |
| Diode Reverse Recovery Charge        | Q <sub>rr</sub>       | -di <sub>F</sub> /dt=200A/μs<br>T <sub>j</sub> =25°C                    | -                     | 0.70 | -    | μC   |    |

#### ■ Equivalent circuit



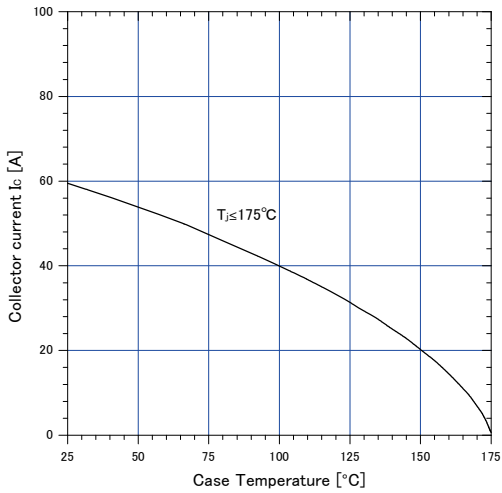
| Items                         | Symbols   | Conditions                                 | Characteristics |      |      | Unit    |
|-------------------------------|-----------|--|-----------------|------|------|---------|
|                               |           |  | min.            | typ. | max. |         |
| Diode Reverse Recovery Time   | $t_{rr2}$ | $V_{CC}=400V$<br>$I_F=25A$                 | -               | 0.44 | -    | $\mu s$ |
| Diode Reverse Recovery Charge | $Q_{rr}$  | $-di_F/dt=200A/\mu s$<br>$T_j=175^\circ C$ | -               | 2.7  | -    | $\mu C$ |

● **Thermal resistance**

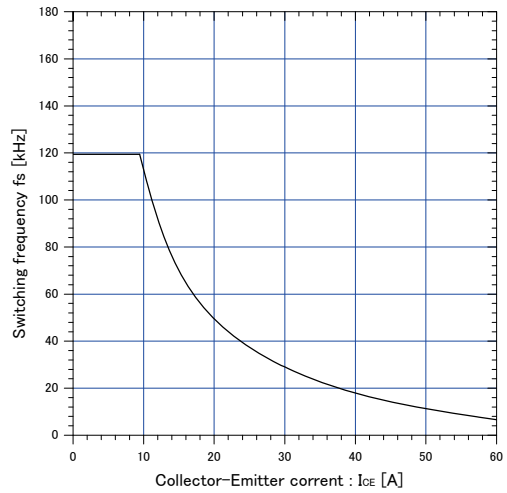
| Items                                     | Symbols              | Characteristics |      |       | Unit         |
|---|----------------------|-----------------|------|-------|--------------|
|   |                      | min.            | typ. | max.  |              |
| Thermal Resistance, Junction-Ambient      | $R_{th(j-a)}$        | -               | -    | 50    | $^\circ C/W$ |
| Thermal Resistance, IGBT Junction to Case | $R_{th(j-c)}_{IGBT}$ | -               | -    | 0.641 |              |
| Thermal Resistance, FWD Junction to Case  | $R_{th(j-c)}_{FWD}$  | -               | -    | 1.191 |              |

■ Characteristics (Representative)

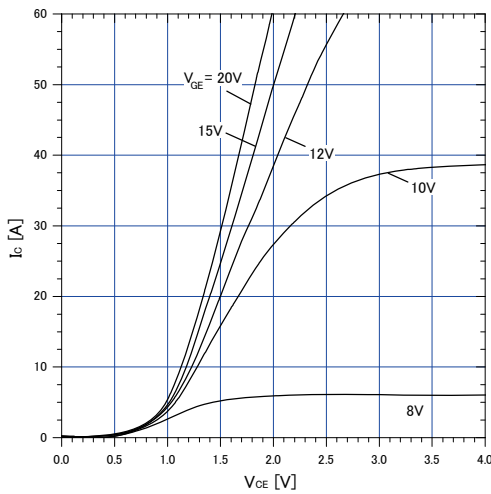
Graph.1  
DC Collector Current vs  $T_c$   
 $V_{GE} \geq +15V, T_j \leq 175^\circ C$



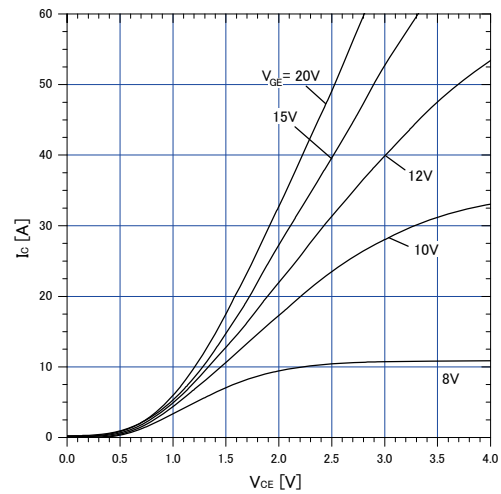
Graph.2  
Collector Current vs. switching frequency  
 $V_{GE} = +15V, T_c \leq 175^\circ C, V_{CC} = 400V, D = 0.5, R_G = 10\Omega, T_c = 100^\circ C$



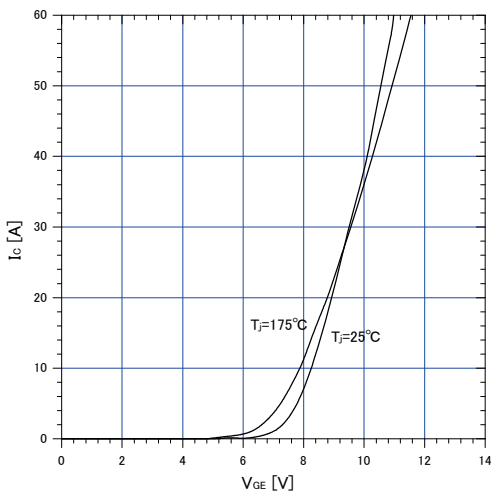
Graph.3  
Typical Output Characteristics ( $V_{CE} - I_c$ )  
 $T_j = 25^\circ C$



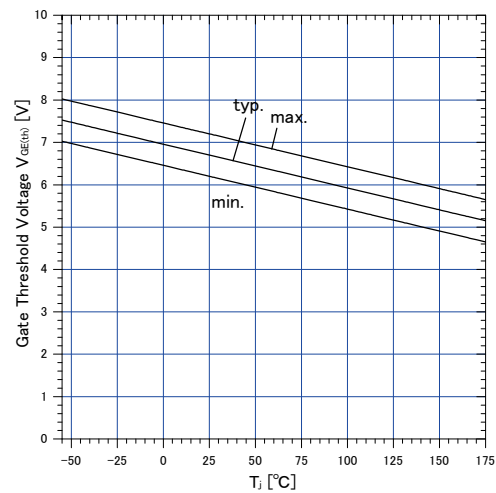
Graph.4  
Typical Output Characteristics ( $V_{CE} - I_c$ )  
 $T_j = 175^\circ C$



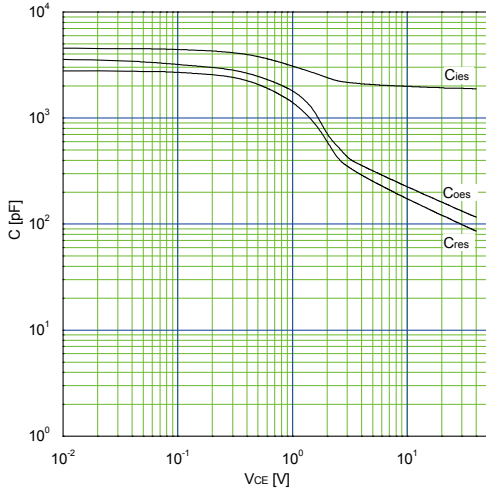
Graph.5  
Typical Transfer Characteristics  
 $V_{GE} = +15V$



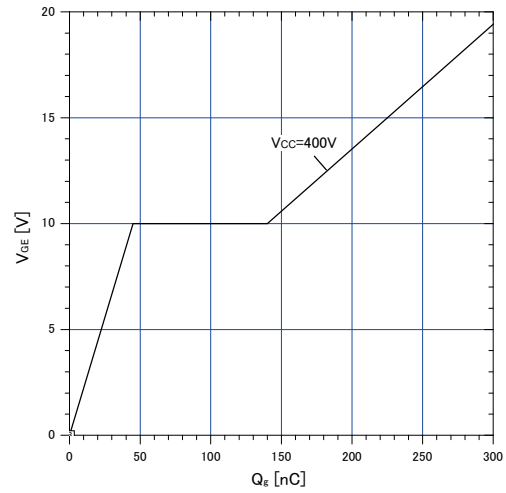
Graph.6  
Gate Threshold Voltage vs.  $T_j$   
 $I_c = 30mA, V_{CE} = 20V$



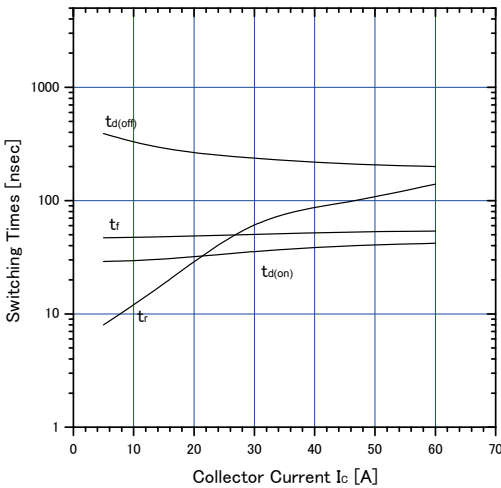
Graph.7  
Typical Capacitance  
 $V_{GE}=0V, f=1MHz, T_j=25^\circ C$



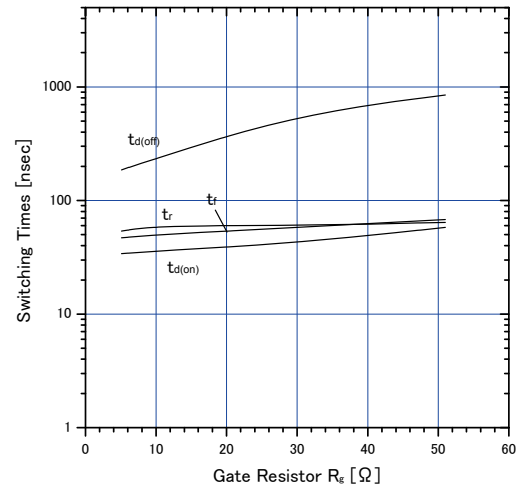
Graph.8  
Typical Gate Charge  
 $V_{CC}=400V, I_c=30A, T_j=25^\circ C$



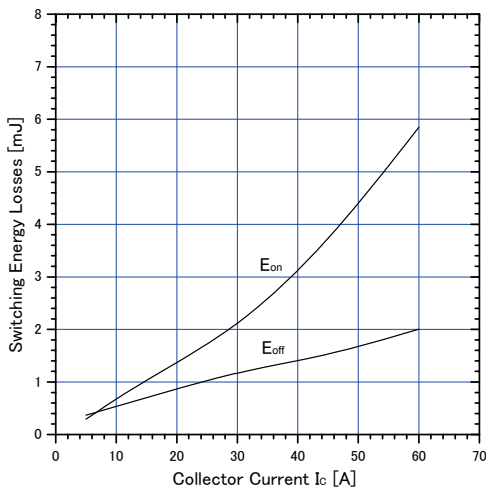
Graph.9  
Typical switching time vs.  $I_c$   
 $T_j=175^\circ C, V_{CC}=400V, L=500\mu H$   
 $V_{GE}=15V, R_G=10\Omega$



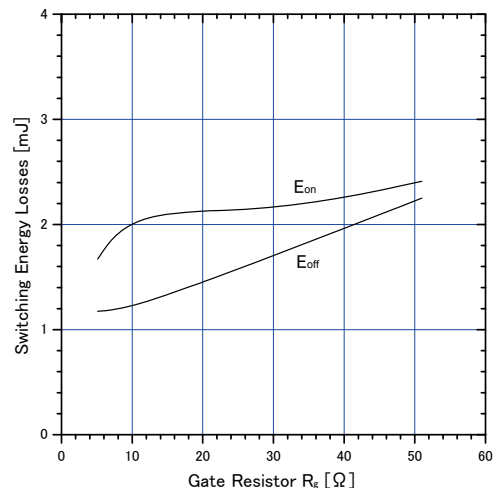
Graph.10  
Typical switching time vs.  $R_G$   
 $T_j=175^\circ C, V_{CC}=400V, I_c=30A, L=500\mu H$   
 $V_{GE}=15V$



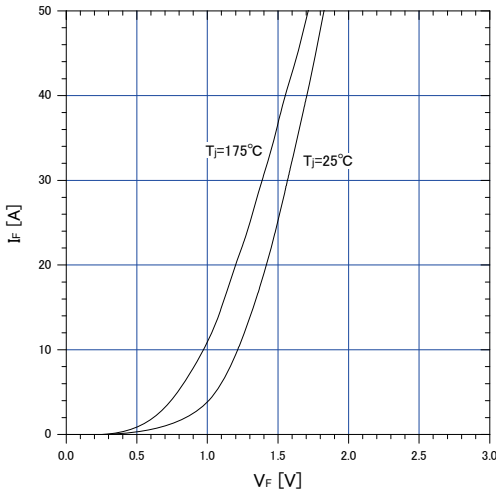
Graph.11  
Typical switching losses vs.  $I_c$   
 $T_j=175^\circ C, V_{CC}=400V, L=500\mu H$   
 $V_{GE}=15V, R_G=10\Omega$



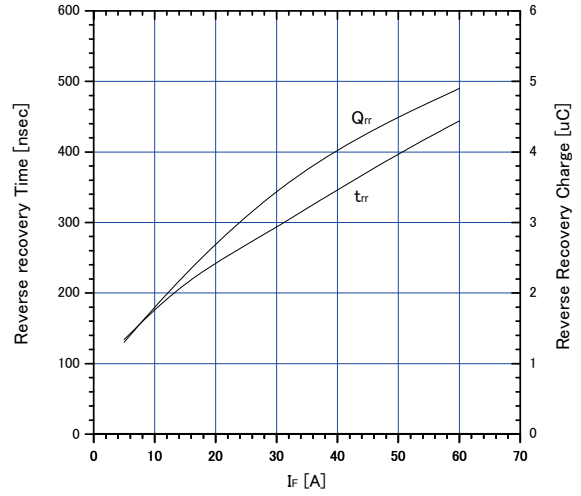
Graph.12  
Typical switching losses vs.  $R_G$   
 $T_j=175^\circ C, V_{CC}=400V, I_c=30A, L=500\mu H$   
 $V_{GE}=15V$



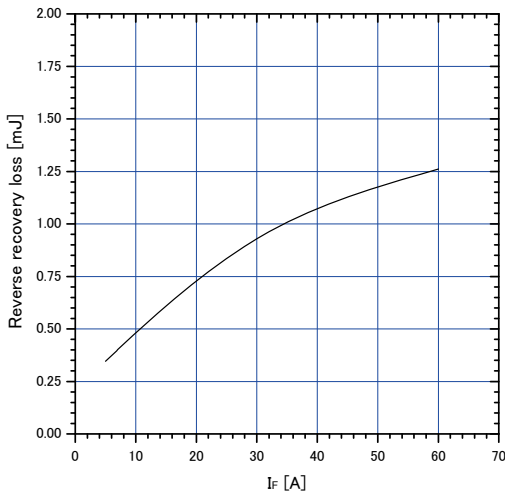
Graph.13  
FWD Forward voltage drop ( $V_F-I_F$ )



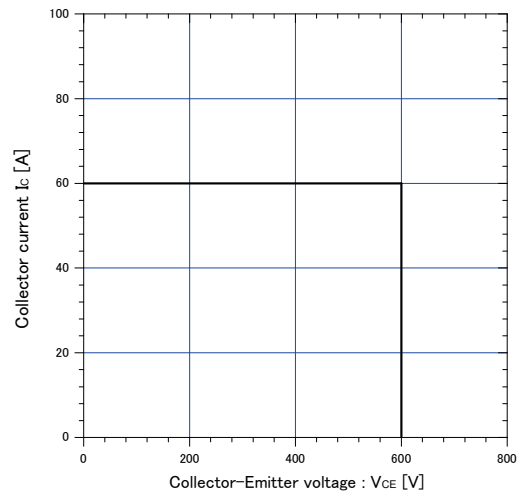
Graph.14  
Typical reverse recovery characteristics vs.  $I_F$   
 $T_J=175^\circ\text{C}$ ,  $V_{CC}=400\text{V}$ ,  $L=500\mu\text{H}$ ,  
 $V_{GE}=15\text{V}$ ,  $R_G=10\Omega$



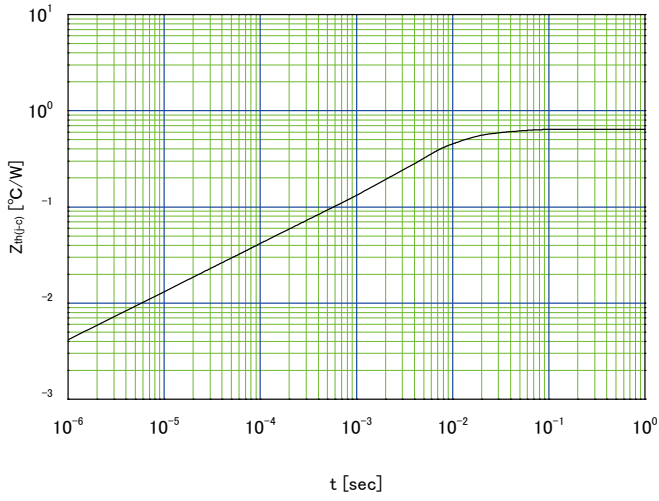
Graph.15  
Typical reverse recovery loss vs.  $I_F$   
 $T_J=175^\circ\text{C}$ ,  $V_{CC}=400\text{V}$ ,  $L=500\mu\text{H}$   
 $V_{GE}=15\text{V}$ ,  $R_G=10\Omega$



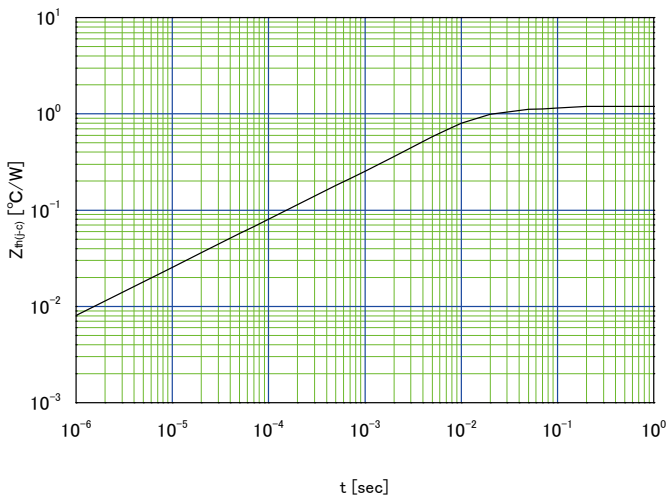
Graph.16  
Reverse biased Safe Operating Area  
 $T_J \leq 175^\circ\text{C}$ ,  $V_{GE}=+15\text{V}/0\text{V}$ ,  $R_G=10\Omega$



Graph.17  
Transient thermal resistance of IGBT

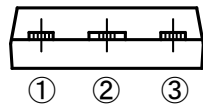
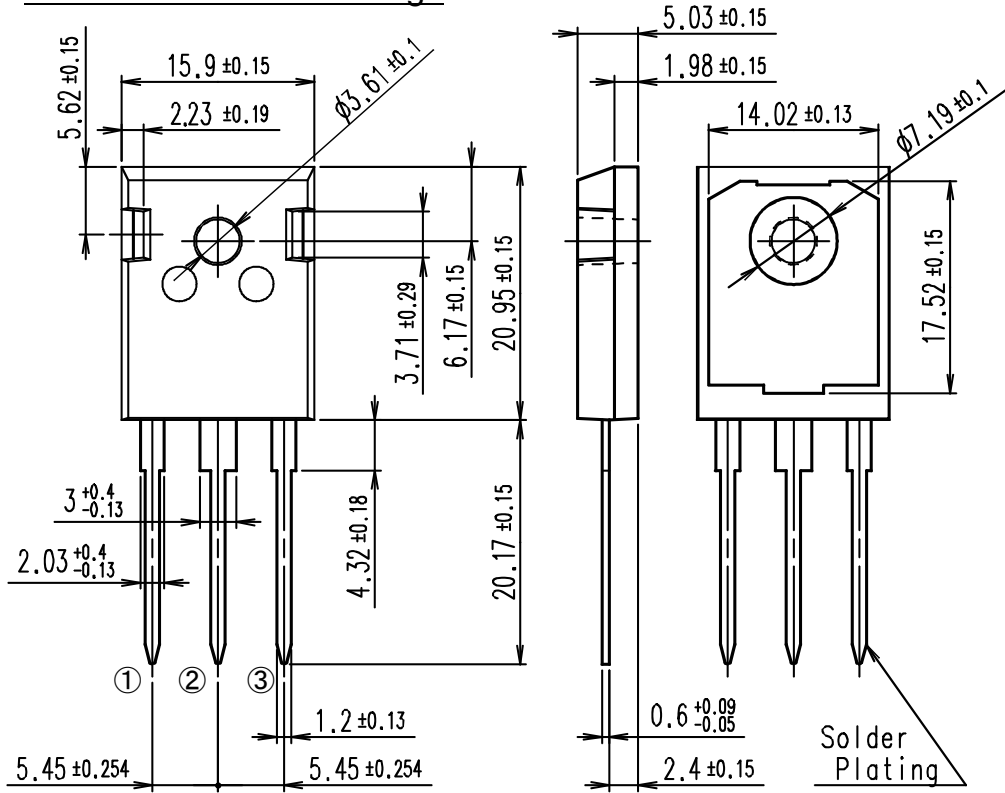


Graph.18  
Transient thermal resistance of FWD



■ Outline Drawings, mm

Outview : TO-247 Package



CONNECTION

- ① GATE
- ② COLLECTOR
- ③ EMITTER

DIMENSIONS ARE IN MILLIMETERS.

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